

1.2V Drive Pch MOSFET

RZE002P02

●Structure

Silicon P-channel MOSFET

●Features

- 1) High speed switching.
- 2) Small package (EMT3).
- 3) 1.2V drive.

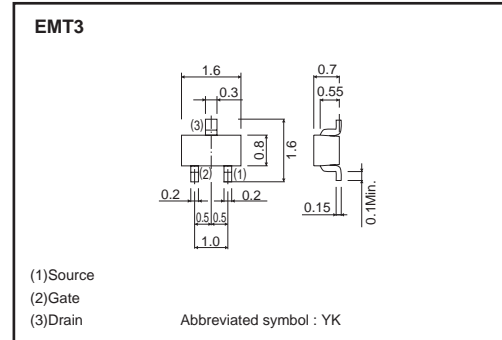
●Applications

Switching

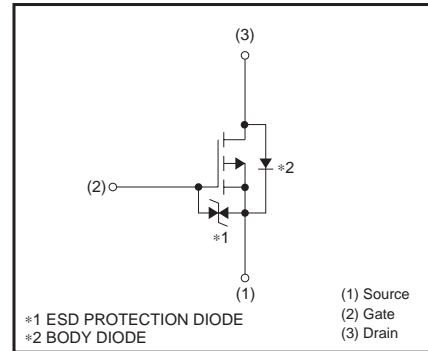
●Package specifications

Type	Package	Taping
	Code	TL
	Basic ordering unit (pieces)	3000
RZE002P02		○

●Dimensions (Unit : mm)



●Inner circuit



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit	
Drain-source voltage	V_{DSS}	-20	V	
Gate-source voltage	V_{GSS}	±10	V	
Drain current	Continuous	I_D	±200	mA
	Pulsed	I_{DP} *1	±800	mA
Source current (Body diode)	Continuous	I_S	-100	mA
	Pulsed	I_{SP} *1	-800	mA
Total power dissipation	P_D *2	150	mW	
Channel temperature	T_{ch}	150	°C	
Range of storage temperature	T_{stg}	-55 to +150	°C	

*1 $P_w \leq 10\mu s$, Duty cycle $\leq 1\%$

*2 Each terminal mounted on a recommended land

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	$R_{th(ch-a)}$ *	833	°C/W

* Each terminal mounted on a recommended land

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	± 10	μA	$V_{GS} = \pm 10V, V_{DS} = 0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	-20	-	-	V	$I_D = -1mA, V_{GS} = 0V$
Zero gate voltage drain current	I_{DSS}	-	-	-1	μA	$V_{DS} = -20V, V_{GS} = 0V$
Gate threshold voltage	$V_{GS(th)}$	-0.3	-	-1.0	V	$V_{DS} = -10V, I_D = -100\mu A$
Static drain-source on-state resistance	$R_{DS(on)}$ *	-	0.8	1.2	Ω	$I_D = -200mA, V_{GS} = -4.5V$
		-	1.0	1.5	Ω	$I_D = -100mA, V_{GS} = -2.5V$
		-	1.3	2.2	Ω	$I_D = -100mA, V_{GS} = -1.8V$
		-	1.6	3.5	Ω	$I_D = -40mA, V_{GS} = -1.5V$
		-	2.4	9.6	Ω	$I_D = -10mA, V_{GS} = -1.2V$
Forward transfer admittance	$ Y_{fs} $ *	0.2	-	-	S	$V_{DS} = -10V, I_D = -200mA$
Input capacitance	C_{iss}	-	115	-	pF	$V_{DS} = -10V$
Output capacitance	C_{oss}	-	10	-	pF	$V_{GS} = 0V$
Reverse transfer capacitance	C_{rss}	-	6	-	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}$ *	-	6	-	ns	$V_{DD} \doteq -10V$
Rise time	t_r *	-	4	-	ns	$I_D = -100mA$ $V_{GS} = -4.5V$
Turn-off delay time	$t_{d(off)}$ *	-	17	-	ns	$R_L \doteq 100\Omega$
Fall time	t_f *	-	17	-	ns	$R_G = 10\Omega$
Total gate charge	Q_g *	-	1.4	-	nC	$V_{DD} \doteq -10V \quad R_L \doteq 50\Omega$
Gate-source charge	Q_{gs} *	-	0.3	-	nC	$I_D = -200mA \quad R_G = 10\Omega$
Gate-drain charge	Q_{gd} *	-	0.3	-	nC	$V_{GS} = -4.5V$

*Pulsed

●Body diode characteristics (Source-drain)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{SD} *	-	-	-1.2	V	$I_S = -200mA, V_{GS} = 0V$

*Pulsed

●Electrical characteristics curves

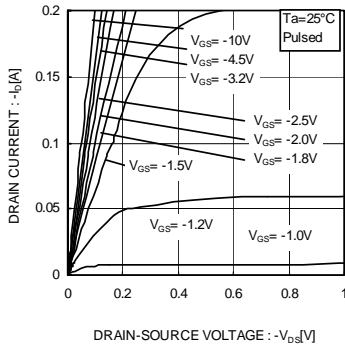


Fig.1 Typical Output Characteristics (I)

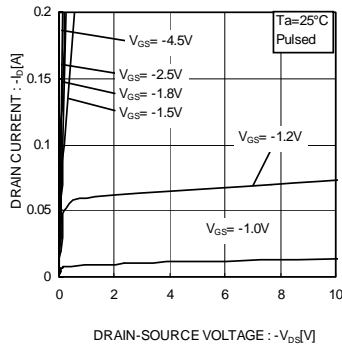


Fig.2 Typical Output Characteristics(II)

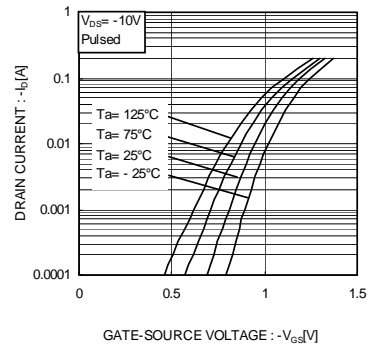


Fig.3 Typical Transfer Characteristics

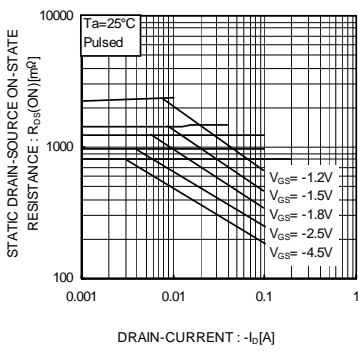


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current(I)

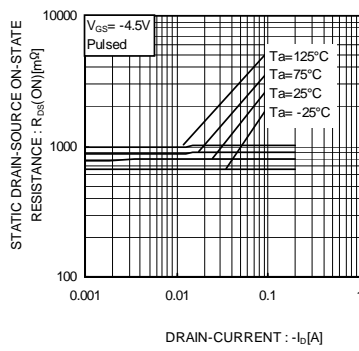


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current(II)

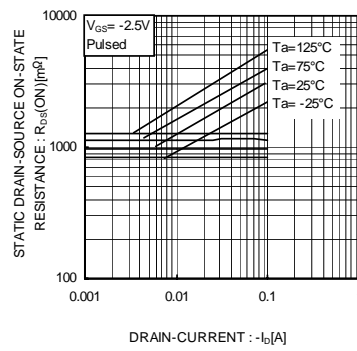


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(III)

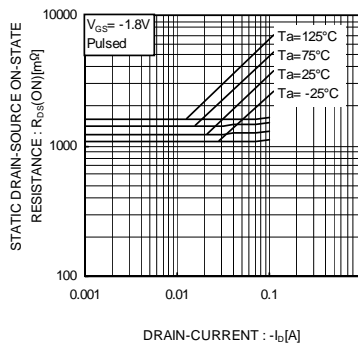


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current(IV)

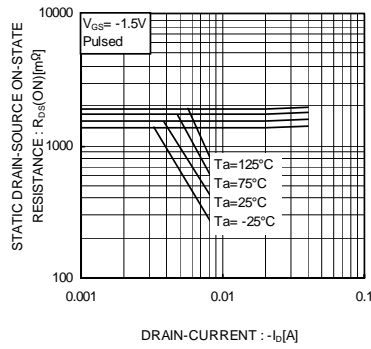


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current(V)

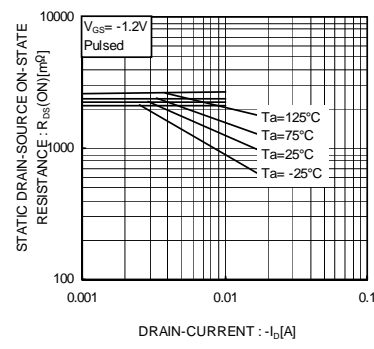


Fig.9 Static Drain-Source On-State Resistance vs. Drain Current(VI)

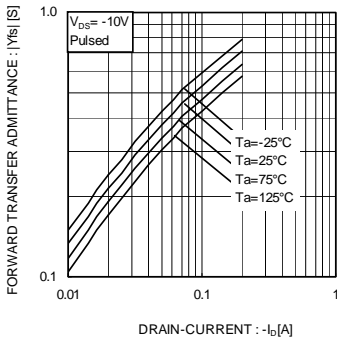


Fig.10 Forward Transfer Admittance vs. Drain Current

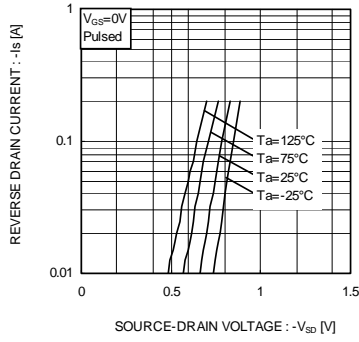


Fig.11 Reverse Drain Current vs. Source-Drain Voltage

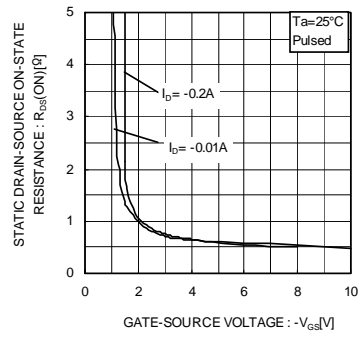


Fig.12 Static Drain-Source On-State Resistance vs. Gate Source Voltage

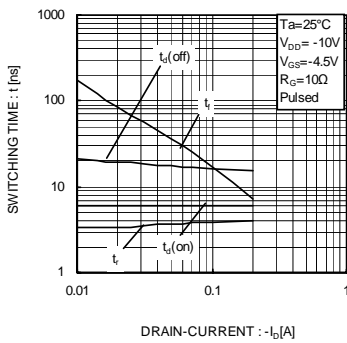


Fig.13 Switching Characteristics

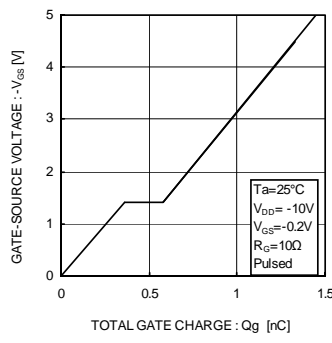


Fig.14 Dynamic Input Characteristics

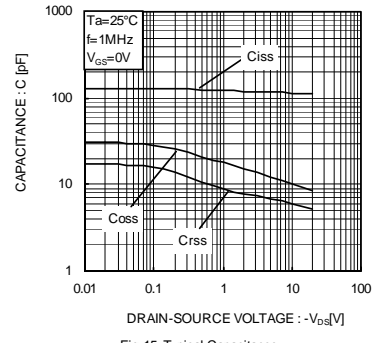


Fig.15 Typical Capacitance vs. Drain-Source Voltage

●Measurement circuit

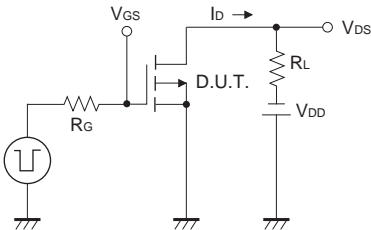


Fig.1-1 Switching Time Measurement Circuit

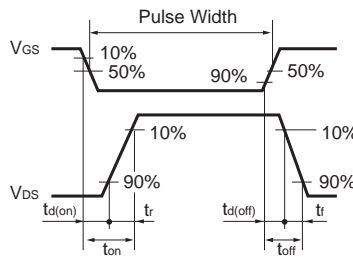


Fig.1-2 Switching Waveforms

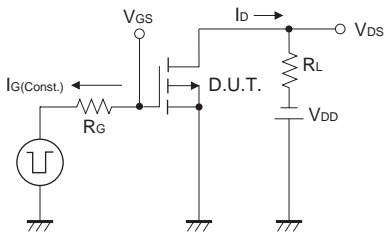


Fig.2-1 Gate Charge Measurement Circuit

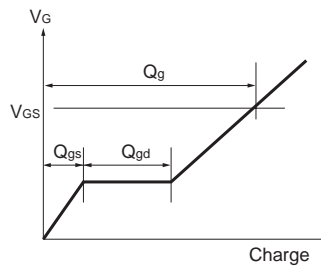


Fig.2-2 Gate Charge Waveform

●Notice

This product might cause chip aging and breakdown under the large electrified environment.

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